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U.S.S.N. 10/791,607

APR 15 2009

In the Claims

Please cancel Claims 29,30 and 41 without prejudice.

Please amend Claims 28,31 and 33 as follows:

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Listing of Claims

Claims 1-25 (canceled)

26. (previously presented) A phase change memory structure comprising:

a substrate comprising a conductive area;

a spacer comprising a phase changing material sensitive to temperature and having a partially exposed sidewall region at the spacer upper portion defining a contact area, said contact area comprising an upward sloping positive radius of curvature; and

an upper conductive electrode on said contact area;

wherein a spacer bottom portion partially overlaps the conductive area and said upper conductive electrode at least partially overlaps said contact area.

27. (original) The phase change memory structure of claim 26, wherein the upper conductive electrode comprises a material selected from the group consisting of W, TiN, TiW, TiAl, TiAlN, and combinations thereof.

28. (currently amended) A phase change memory structure comprising:

a substrate comprising a conductive area;

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a spacer having a partially exposed sidewall region at the spacer upper portion defining a contact area, said contact area comprising an upward sloping positive radius of curvature, an upper conductive electrode at least partially overlaps said contact area;

wherein the spacer comprises ~~a material selected from the group consisting of a conductive material and a phase changing material sensitive to temperature;~~ said spacer further comprises a memory element, and,

wherein a spacer bottom portion at least partially overlaps the conductive area.

Claims 29-30 (canceled)

31. (currently amended) The phase change memory structure of claim 30 28, wherein the phase changing material comprises a chalcogenide.

32. (original) The phase change memory structure of claim 31, wherein the chalcogenide comprises a material selected from the group consisting of Ge, Te, and Sb and their alloy system.

33. (currently amended) The phase change memory structure of claim 30 28, wherein the upper conductive electrode comprises a

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material selected from the group consisting of W, TiN, TiW, TiAl, TiAlN, and combinations thereof.

Claims 34-41 (canceled)